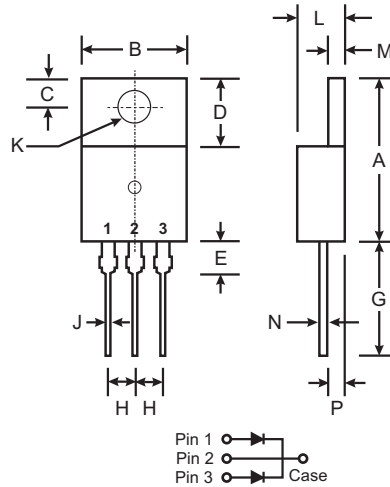


### Features

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- Low Power Loss, High Efficiency
- High Surge Capability
- High Current Capability and Low Forward Voltage Drop
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications
- **Lead Free Finish, RoHS Compliant (Note 3)**

### Mechanical Data

- Case: TO-220AB
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish – Bright Tin. Solderable per MIL-STD-202, Method 208
- Polarity: As Marked on Body
- Marking: Type Number
- Weight: 2.24 grams (approx.)



TO-220AB		
Dim	Min	Max
A	14.48	15.75
B	10.00	10.40
C	2.54	3.43
D	5.90	6.40
E	2.80	3.93
G	12.70	14.27
H	2.40	2.70
J	0.69	0.93
K	3.54	3.78
L	4.07	4.82
M	1.15	1.39
N	0.30	0.50
P	2.04	2.79
All Dimensions in mm		

### Maximum Ratings and Electrical Characteristics @ T<sub>A</sub> = 25°C unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load.  
For capacitive load, derate current by 20%.

Characteristic	Symbol	MBR 1530CT	MBR 1535CT	MBR 1540CT	MBR 1545CT	MBR 1550CT	MBR 1560CT	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	30	35	40	45	50	60	V
RMS Reverse Voltage	V <sub>R(RMS)</sub>	21	24.5	28	31.5	35	42	V
Average Rectified Output Current @ T <sub>C</sub> = 125°C (Note 1)	I <sub>O</sub>	15						A
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I <sub>FSM</sub>	150						A
Forward Voltage Drop @ I <sub>F</sub> = 15A, T <sub>C</sub> = 125°C @ I <sub>F</sub> = 7.5A, T <sub>C</sub> = 125°C @ I <sub>F</sub> = 15A, T <sub>C</sub> = 25°C	V <sub>FM</sub>	0.72 0.57 0.84				0.80 0.65 0.90		V
Peak Reverse Current at Rated DC Blocking Voltage @ T <sub>C</sub> = 25°C @ T <sub>C</sub> = 125°C	I <sub>RM</sub>	0.1 15				1.0 50		mA
Typical Total Capacitance (Note 2)	C <sub>T</sub>	300						pF
Typical Thermal Resistance Junction to Case (Note 1)	R <sub>θJc</sub>	1.7						°C/W
Voltage Rate of Change (Rated V <sub>R</sub> )	dV/dt	1000			10,000			V/μs
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-65 to +150						°C

- Notes:
1. Thermal resistance junction to case mounted on heatsink.a
  2. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.
  3. RoHS revision 13.2.2003. Glass and High Temperature Solder Exemptions Applied, see EU Directive Annex Notes 5 and 7.

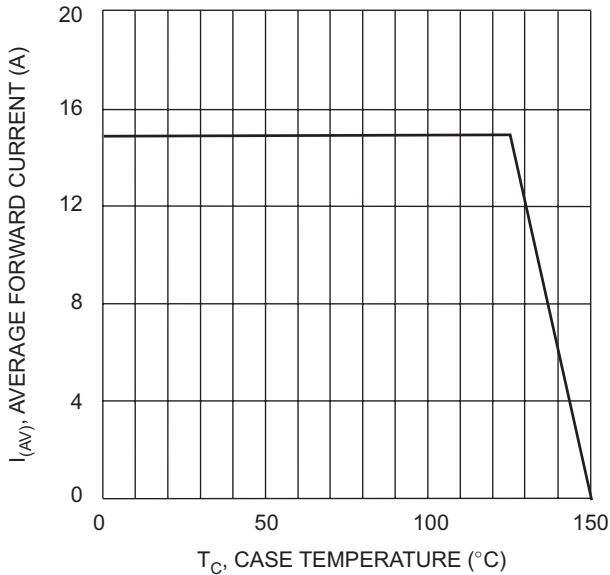


Fig. 1 Forward Current Derating Curve

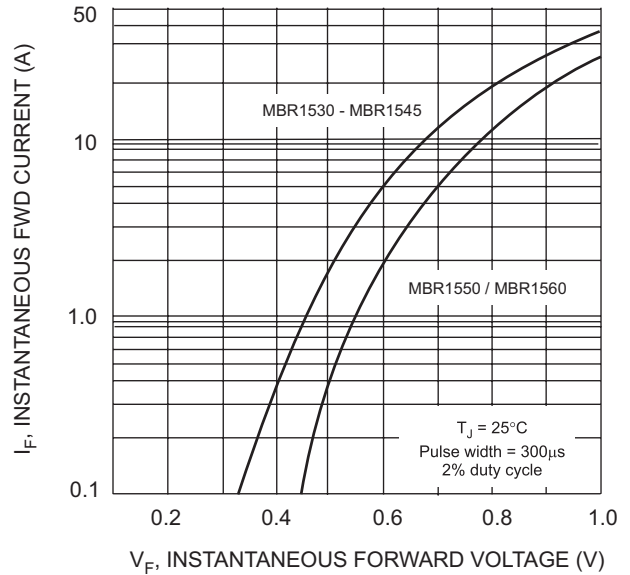


Fig. 2 Typical Forward Characteristics

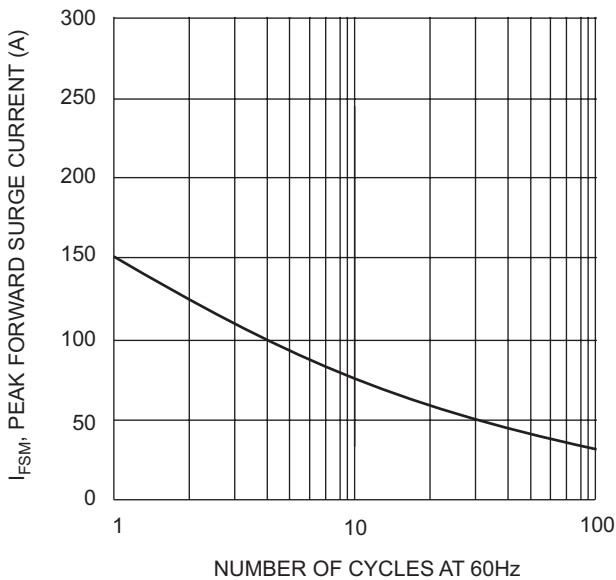


Fig. 3 Max Non-Repetitive Surge Current

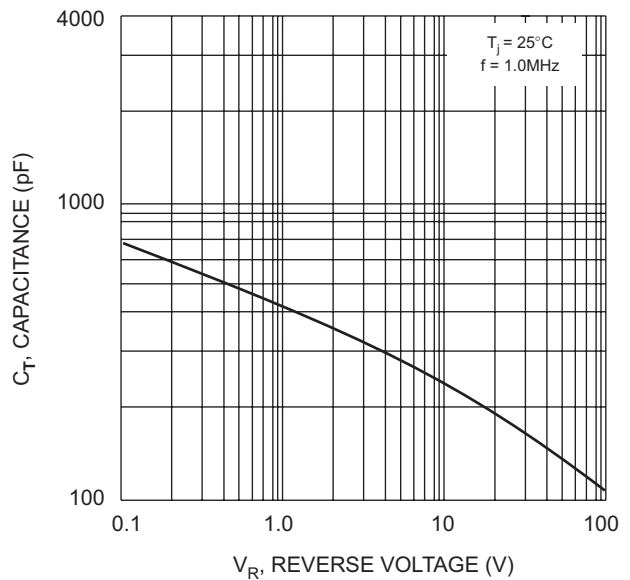


Fig. 4 Typical Total Capacitance (per element)

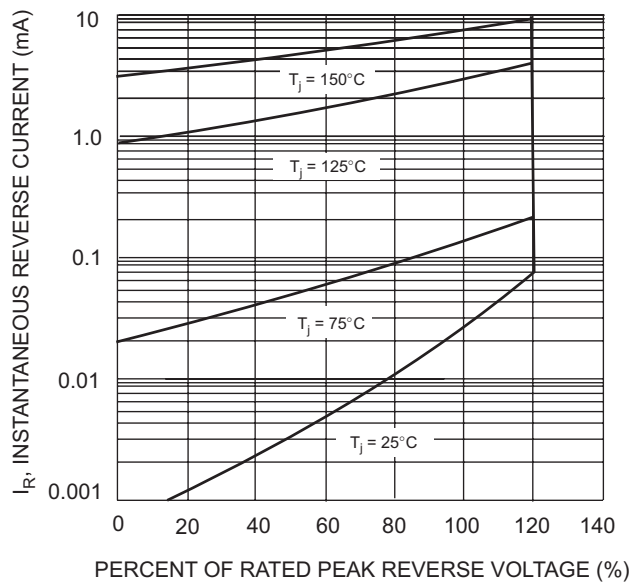


Fig. 5 Typical Reverse Characteristics

**Ordering Information** (Note 4)

Device	Packaging	Shipping
MBR15xxCT*	TO-220AB	50/Tube

\* xx = Device type, e.g. MBR1545CT

Notes: 4. For Packaging Details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.